

EH3620TS-33.333M **ITEM DESCRIPTION**

Quartz Crystal Clock Oscillators XO (SPXO) LVCMOS (CMOS) 3.3Vdc 4 Pad 3.2mm x 5.0mm Ceramic Surface Mount (SMD)
33.333MHz ± 20 ppm 0°C to +70°C

ELECTRICAL SPECIFICATIONS

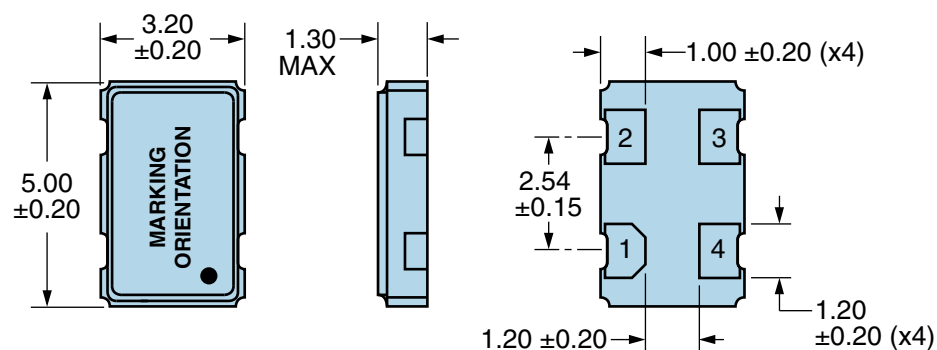
Nominal Frequency	33.333MHz
Frequency Tolerance/Stability	± 20 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, 1st Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	± 5 ppm/year Maximum
Operating Temperature Range	0°C to +70°C
Supply Voltage	3.3Vdc $\pm 10\%$
Input Current	35mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.7Vdc Minimum (IOH = -8mA)
Output Voltage Logic Low (Vol)	0.5Vdc Maximum (IOL = +8mA)
Rise/Fall Time	6nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 $\pm 10\%$ (Measured at 50% of waveform)
Load Drive Capability	30pF Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	70% of Vdd Minimum to enable output, 20% of Vdd Maximum to disable output, No Connect to enable output.
Absolute Clock Jitter	± 250 pSec Maximum, ± 100 pSec Typical
One Sigma Clock Period Jitter	± 50 pSec Maximum, ± 40 pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010
Vibration	MIL-STD-883, Method 2007, Condition A

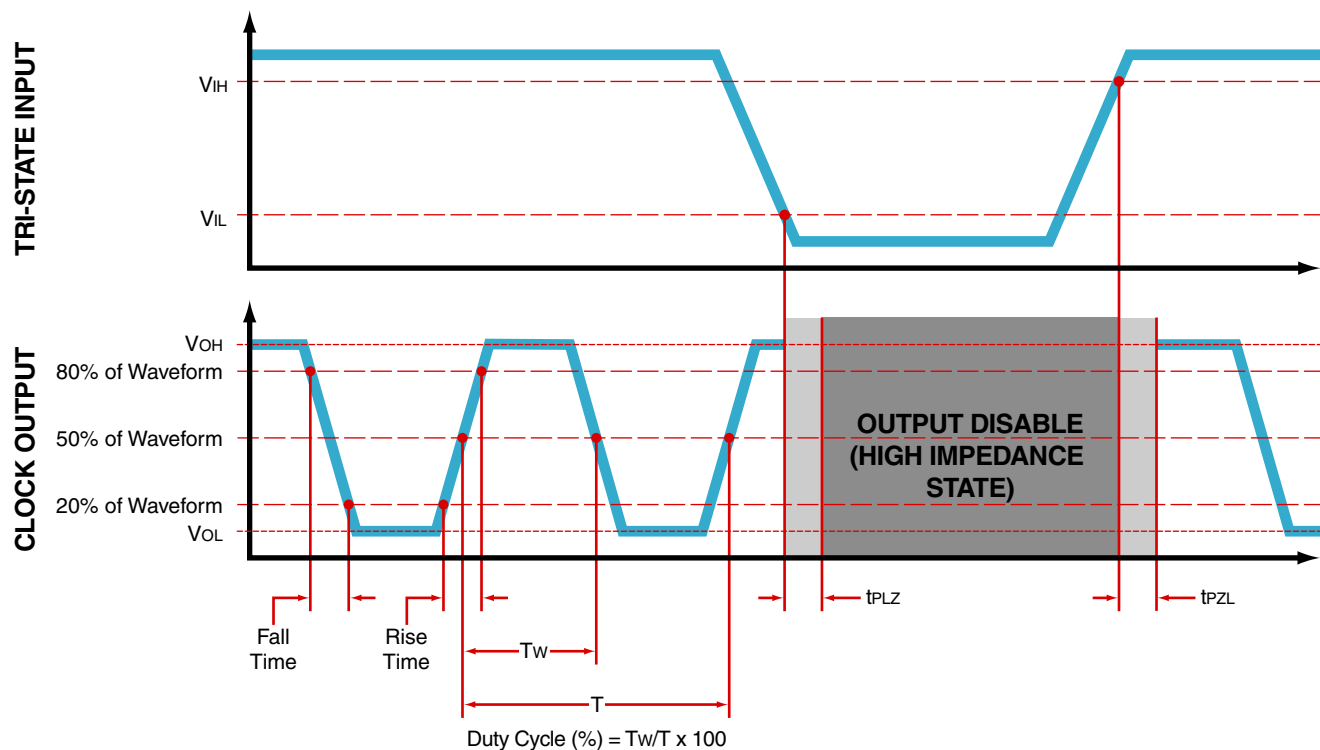
EH3620TS-33.333M

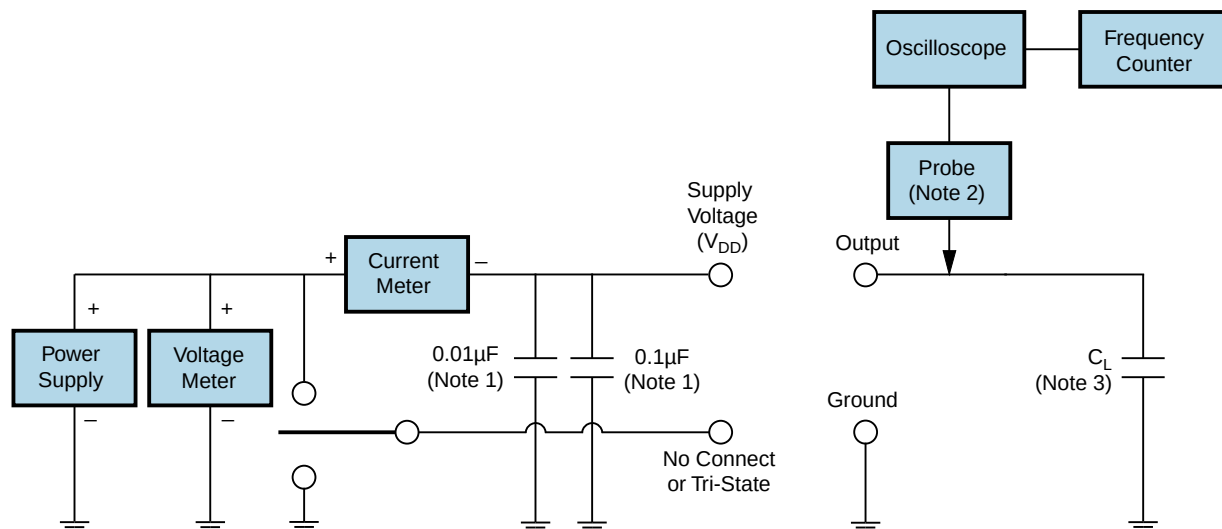
MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Ground/Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	E33.333 <i>E=Ecliptek Designator</i>
2	XXXXX <i>XXXXX=Ecliptek Manufacturing Identifier</i>

OUTPUT WAVEFORM & TIMING DIAGRAM

Test Circuit for CMOS Output

Note 1: An external 0.1 μ F low frequency tantalum bypass capacitor in parallel with a 0.01 μ F high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.